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•	Meets or Exceeds the Requirements of ANSI EIA/TIA-232-E and ITU Recommendation V.28	DW OR N PACKAGE (TOP VIEW)
•	Single Chip With Easy Interface Between UART and Serial Port Connector	V _{DD} 1 20 V _{CC} RA1 2 19 RY1
•	Less Than 9-mW Power Consumption	RA2 [] 3 18 [] RY2 RA3 [] 4 17 [] RY3
٠	Wide Driver Supply Voltage 4.5 V to 13.2 V	RA3 [] 4 17 [] RY3 DY1 [] 5 16] DA1 DY2 [] 6 15 [] DA2
•	Driver Output Slew Rate Limited to 30 V/μs Max	RA4 [] 7 14]] RY4 DY3 [] 8 13 [] DA3
٠	Receiver Input Hysteresis 1100 mV Typ	RA5 🛛 9 12 🗍 RY5
•	Push-Pull Receiver Outputs	V _{SS} [10 11] GND
•	On-Chip Receiver 1-μs Noise Filter	

• Functionally Interchangeable With Texas Instruments SN75185

description

The SN75C185 is a low-power BiMOS device containing three independent drivers and five receivers that are used to interface data terminal equipment (DTE) with data circuit-terminating equipment (DCE). The SN75C185 will typically replace one SN75188 and two SN75189 devices. This device is designed to conform to ANSI Standards EIA/TIA-232-E. The three drivers and five receivers of the SN75C185 are similar to those of the SN75C188 quad drivers and SN75C189A quad receivers, respectively. The drivers have a controlled output slew rate that is limited to a maximum of 30 V/ μ s and the receivers have filters that reject input noise pulses that are shorter than 1 μ s. Both these features eliminate the need for external components.

The SN75C185 has been designed using low-power techniques in a BiMOS technology. In most applications, the receivers contained in this device will interface to single inputs of peripheral devices such as ACEs, UARTS, or micro-processors. By using sampling, such peripheral devices are usually insensitive to the transition times of the input signals. If this is not the case, or for other uses, it is recommended that the SN75C185 receiver outputs be buffered by single Schmitt input gates or single gates of the HCMOS, ALS, or 74F logic families.

The SN75C185 is characterized for operation from 0°C to 70°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

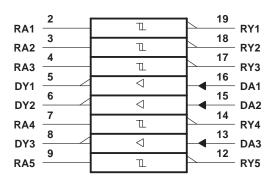
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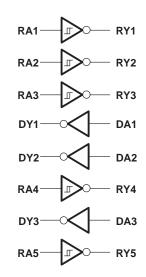
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logic symbol[†]



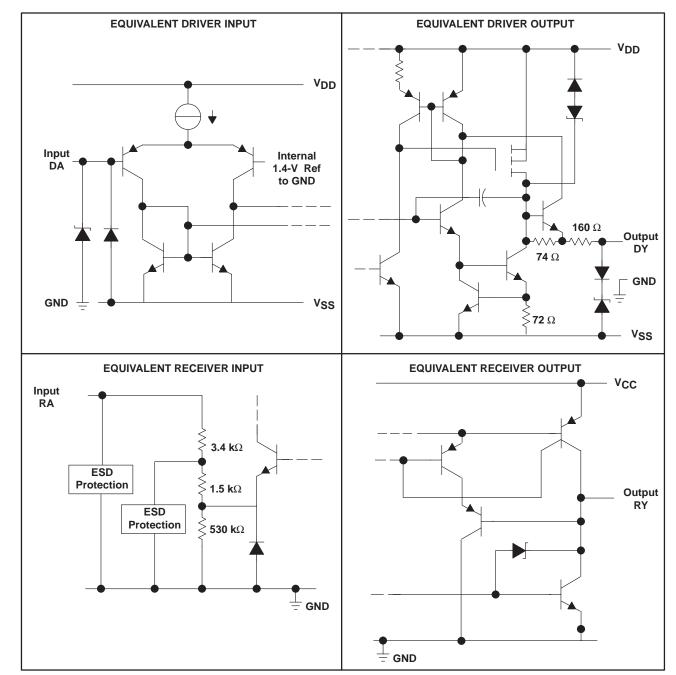
[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





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equivalent schematics of inputs and outputs

All resistor values are nominal.



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage, V _{DD} (see Note 1)	
Supply voltage, V _{CC}	
Input voltage range, VI: Driver	
Receiver	30 V to 30 V
Output voltage range, V _O : Driver	\dots V _{SS} -6 V to V _{DD} + 6 V
Receiver	$\dots \dots $
Continuous total dissipation	See Dissipation Rating Table
Operating free-air temperature range, T _A	0°C to 70°C
Storage temperature range, T _{stg}	–65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	

⁺ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltages are with respect to the network ground terminal.

DISSIPATION RATING TABLE

PACKAGE	PACKAGE $T_A \le 25^{\circ}C$ POWER RATING		T _A ≤ 75°C POWER RATING		
DW	1125 mW	9.0 mW/°C	720 mW		
N	1150 mW	9.2 mW/°C	736 mW		

recommended operating conditions

		MIN	NOM	MAX	UNIT
Supply voltage, V _{DD}		4.5	12	13.2	V
Supply voltage, V _{SS}		-4.5	-12	-13.2	V
Supply voltage, V _{CC}		4.5	5	6	V
Input voltage V/v (and Note 2)	Driver	V _{SS} +2		V _{DD}	V
Input voltage, V _I (see Note 2) Receiver	Receiver	-25		25	v
High-level input voltage, VIH	Driver	2			V
Low-level input voltage, VIL	Diver			0.8	v
High-level output current, IOH	Pagaiyar			-1	mA
High-level output current, IOL	Receiver			3.2	mA
Operating free-air temperature, TA		0		70	°C

NOTE 2: The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only, e.g., if -10 V is a maximum, the typical value is a more negative voltage.

supply currents

	PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
		No load, V All inputs at 2 V or 0.8 V	V _{DD} = 5 V,	$V_{SS} = -5 V$		115	200	
^I DD	Supply current from VDD		V _{DD} = 12 V,	$V_{SS} = -12 V$		115	200	μA
	Supply surrent from Vee	No load,		$V_{SS} = -5 V$		-115	-200	μA
ISS	ISS Supply current from VSS All inj	All inputs at 2 V or 0.8 V $$	V _{DD} = 12 V,	$V_{SS} = -12 V$		-115	-200	μΑ
	Supply surrent from Vee	No load	V _{DD} = 5 V,	$V_{SS} = -5 V$			750	
1CC	Supply current from V _{CC}	All inputs at 0 or 5 V	V _{DD} = 12 V,	$V_{SS} = -12 V$			750	μA



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DRIVER SECTION

electrical characteristics over operating free-air temperature range, V_{DD} = 12 V, V_{SS} = –12 V, V_{CC} = 5 V $\pm 10\%$ (unless otherwise noted)

	PARAMETER		TEST C	ONDITIONS		MIN	TYP†	MAX	UNIT
Vall	High-level output voltage	VIL = 0.8 V,	RL = 3 kΩ,	V _{DD} = 5 V,	$V_{SS} = -5 V$	4	4.5		V
VOH	High-level output voltage	See Figure 1		V _{DD} = 12 V	$V_{SS} = -12 V$	10	10.8		v
Vai	Low-level output voltage	VIH = 0.8 V,	$V_{\rm IH} = 0.8 \text{ V}, \text{ R}_{\rm L} = 3 \text{ k}\Omega, \text{ V}_{\rm L}$		$V_{SS} = -5 V$		-4.4	-4	V
VOL	(see Note 2)	See Figure 1		V _{DD} = 12 V	$V_{SS} = -12 V$		-10.7	-10	v
Iн	High-level input current	V _I = 5 V, See Figure 2					1	μA	
١ _{IL}	Low-level input current	$V_{I} = 0,$	VI = 0, See Figure 2					-1	μA
IOS(H)	High-level short-circuit output current (see Note 3)	V _I = 0.8 V, See Flgure 1				-4.5	-12	-19.5	mA
IOS(L)	Low-level short-circuit output current (see Note 3)	$V_I = 2 V$, $V_O = 0 \text{ or } V_O = V_{DD}$, See Figure 1			4.5	12	19.5	mA	
r _o	Output resistance	V _{DD} = V _{SS} = See Note 4	V _{CC} = 0,	$V_{O} = -2 V to$	2 V,	300	400		Ω

[†] All typical values are at $T_A = 25 \,^{\circ}C$.

NOTES: 2. The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only, e.g., if -10 V is a maximum, the typical value is a more negative voltage.

3. Not more than one output should be shorted at one time.

4. Test conditions are those specified by EIA/TIA-232-E.

switching characteristics, V_{DD} = 12 V, V_{SS} = –12 V, V_{CC} = 5 V $\pm 10\%,$ T_A = 25°C (unless otherwise noted)

	PARAMETER	TEST CONDI	MIN	TYP	MAX	UNIT	
^t PLH	Propagation delay time, low- to high-level output (see Note 5)				1.2	3	μs
^t PHL	Propagation delay time, high- to low-level output (see Note 5)	$R_L = 3 k\Omega$ to 7 kΩ, See Figure 3	C _L = 15 pF,		2.5	3.5	μs
^t TLH	Transition time, low- to high-level output	1		0.53	2	3.2	μs
^t THL	Transition time, high- to low-level output			0.53	2	3.2	μs
t _{TLH}	Transition time, low- to high-level output (see Note 6)	$R_L = 3 k\Omega$ to 7 k Ω ,	CL = 2500 pF,		1		μs
t _{THL}	Transition time, high- to low-level output (see Note 6)	See Figure 3			1		μs
S _R	Output slew rate (see Note 6)	$R_L = 3 k\Omega$ to 7 k Ω , See Figure 3	C _L = 15 pF,	4	10	30	V/µs

NOTES: 5. tPHL and tPLH include the additional time due to on-chip slew rate and are measured at the 50% points.

6. Measured between 3-V and –3-V points of output waveform (EIA/TIA-232-E conditions), all unused inputs tied either high or low.



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RECEIVER SECTION

electrical characteristics over operating free-air temperature range, V_{DD} = 12 V, V_{SS} = –12 V, V_{CC} = 5 V $\pm 10\%$ (unless otherwise noted)

	PARAMETER		TEST COND	ITIONS	MIN	TYP†	MAX	UNIT	
V _{IT+}	Positive-going input threshhold voltage	See Figure 5			1.6	2.1	2.55	V	
V _{IT-}	Negative-going input threshhold voltage	See Figure 5			0.65	1	1.25	V	
V _{hys}	Input hysteresis voltage (V _{IT +} - V _{IT} _)				600	1100		mV	
	High-level output voltage	V _I = 0.75 V,	$I_{OH} = -20 \ \mu A$,	See Figure 5 and Note 7	3.5				
Varia		$V_I = 0.75 V$, $I_{OH} = -1 mA$, See Figure 5	$V_{CC} = 4.5 V$		2.8	4.4		V	
VOH			$V_{CC} = 5 V$		3.8	4.9		v	
			V _{CC} = 5.5 V		4.3	5.4			
VOL	Low-level output voltage	V _I = 3 V,	I _{OL} = 3.2 mA,	See Figure 5		0.17	0.4	V	
1		V _I = 3 V			0.43	0.55	1		
lΉ	High-level input current	V _I = 25 V			3.6	4.6	8.3	mA	
1		V _I = -3 V			-0.43	-0.55	-1		
۱L	Low-level input current	V _I = -25 V			-3.6	-5.0	-8.3	mA	
IOS(H)	Short-circuit output at high level	V _I = 0.75 V,	V _O = 0,	See Figure 4		-8	-15	mA	
IOS(L)	Short-circuit output at low level	$V_{I} = V_{CC},$	$V_{O} = V_{CC},$	See Figure 4		13	25	mA	

[†] All typical values are at $T_A = 25 \,^{\circ}C$.

NOTE 7: If the inputs are left unconnected, the receiver interprets this as an input low, and the receiver outputs remain in the high state.

switching characteristics, V_{DD} = 12 V, V_{SS} = –12 V, V_{CC} = 5 V $\pm 10\%,$ T_A = 25°C (unless otherwise noted)

	PARAMETER		TEST CONDITIONS			TYP	MAX	UNIT
^t PLH	Propagation delay time, low- to high-level output					3	4	μs
^t PHL	Propagation delay time, high- to low-level output	$\mathbf{P}_{i} = \mathbf{F}_{i} \mathbf{k}_{0}$	$C_{1} = 50 \text{ pE}$	Soo Eiguro 6		3	4	μs
^t TLH	Transition time, low- to high-level output	κ <u>Γ</u> = 5 κΩ,	$C_{L} = 50 \text{pF},$	See Figure o		300	450	ns
^t THL	Transition time, high- to low-level output					100	300	ns
^t w(N)	Duration of longest pulse rejected as noise (see Note 8)	$R_L = 5 k\Omega$,	C _L = 50 pF,	See Figure 6	1		4	μs

NOTE 8: The receiver ignores any postive- or negative-going pulse that is less than the minimum value of $t_{W(N)}$ and accepts any positive- or negative-going pulse greater than the maximum of $t_{W(N)}$.



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PARAMETER MEASUREMENT INFORMATION

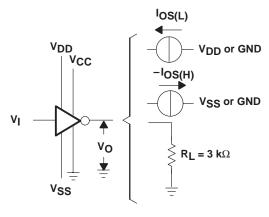


Figure 1. Driver Test Circuit for V_{OH} , V_{OL} , $I_{OS(H)}$, and $I_{OS(L)}$

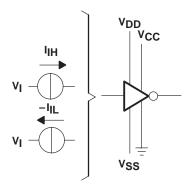
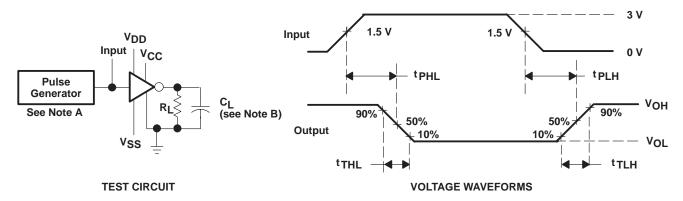


Figure 2. Driver Test Circuit for IIH and IIL



NOTES: A. The pulse generator has the following characteristics: $t_W = 25 \ \mu$ s, PRR = 20 kHz, $Z_O = 50 \ \Omega$, $t_f = t_f < 50 \ ns$. B. CL includes probe and jig capacitance.

Figure 3. Driver Test Circuit and Voltage Waveforms



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PARAMETER MEASUREMENT INFORMATION

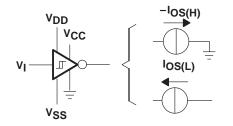


Figure 4. Receiver Test Circuit for IOS(H) and IOS(L)

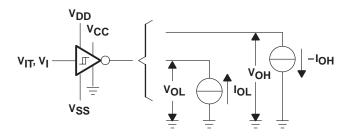
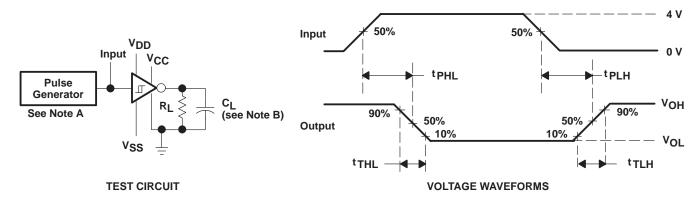


Figure 5. Receiver Test Circuit for V_{IT} , V_{OH} , and V_{OL}



NOTES: A. The pulse generator has the following characteristics: $t_W = 25 \ \mu s$, PRR = 20 kHz, $Z_O = 50 \ \Omega$, $t_f = t_f < 50 \ ns$. B. CL includes probe and jig capacitance.

Figure 6. Receiver Propagation and Transition Times



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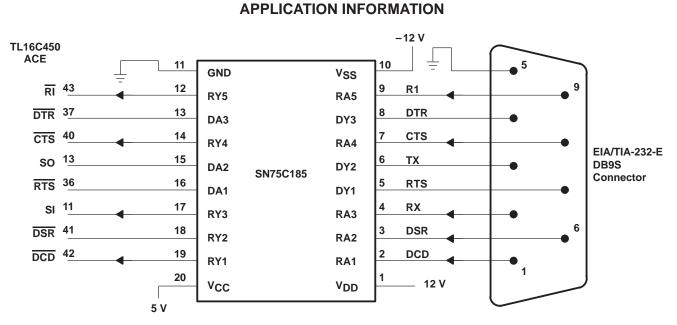


Figure 7. Typical Connection



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